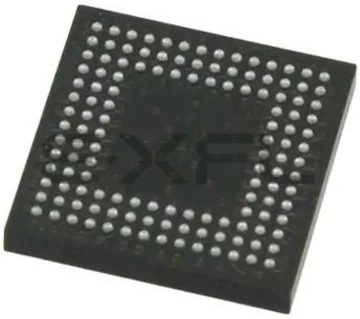
Lattice Semiconductor Corporation - LCMXO2-2000ZE-3MG132I Datasheet



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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Active
Number of LABs/CLBs	264
Number of Logic Elements/Cells	2112
Total RAM Bits	75776
Number of I/O	104
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	132-LFBGA, CSPBGA
Supplier Device Package	132-CSPBGA (8x8)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lcmxo2-2000ze-3mg132i

Modes of Operation

Each slice has up to four potential modes of operation: Logic, Ripple, RAM and ROM.

Logic Mode

In this mode, the LUTs in each slice are configured as 4-input combinatorial lookup tables. A LUT4 can have 16 possible input combinations. Any four input logic functions can be generated by programming this lookup table. Since there are two LUT4s per slice, a LUT5 can be constructed within one slice. Larger look-up tables such as LUT6, LUT7 and LUT8 can be constructed by concatenating other slices. Note LUT8 requires more than four slices.

Ripple Mode

Ripple mode supports the efficient implementation of small arithmetic functions. In Ripple mode, the following functions can be implemented by each slice:

- Addition 2-bit
- Subtraction 2-bit
- Add/subtract 2-bit using dynamic control
- Up counter 2-bit
- Down counter 2-bit
- Up/down counter with asynchronous clear
- Up/down counter with preload (sync)
- Ripple mode multiplier building block
- Multiplier support
- Comparator functions of A and B inputs
    - A greater-than-or-equal-to B
    - A not-equal-to B
    - A less-than-or-equal-to B

Ripple mode includes an optional configuration that performs arithmetic using fast carry chain methods. In this configuration (also referred to as CCU2 mode) two additional signals, Carry Generate and Carry Propagate, are generated on a per-slice basis to allow fast arithmetic functions to be constructed by concatenating slices.

RAM Mode

In this mode, a 16x4-bit distributed single port RAM (SPR) can be constructed by using each LUT block in Slice 0 and Slice 1 as a 16x1-bit memory. Slice 2 is used to provide memory address and control signals.

MachXO2 devices support distributed memory initialization.

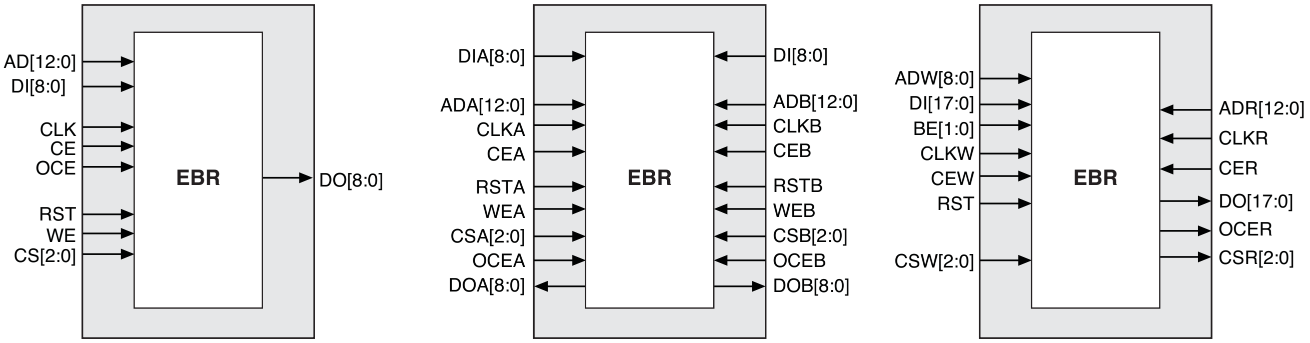
The Lattice design tools support the creation of a variety of different size memories. Where appropriate, the software will construct these using distributed memory primitives that represent the capabilities of the PFU. Table 2-3 shows the number of slices required to implement different distributed RAM primitives. For more information about using RAM in MachXO2 devices, please see TN1201, Memory Usage Guide for MachXO2 Devices.

Table 2-3. Number of Slices Required For Implementing Distributed RAM

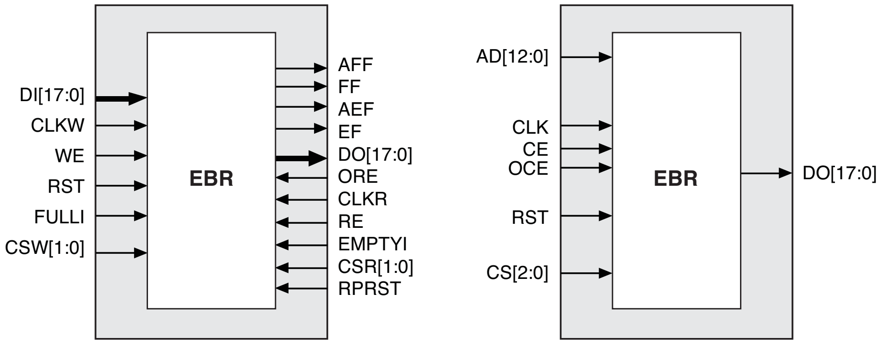
	SPR 16x4	**PDPR 16x4**
Number of slices	3	3

Note: SPR = Single Port RAM, PDPR = Pseudo Dual Port RAM

Figure 2-8. sysMEM Memory Primitives



Single-Port RAM **True Dual Port RAM** **Pseudo Dual Port RAM**



FIFO RAM **ROM**

Table 2-6. EBR Signal Descriptions

Port Name	Description	Active State
CLK	Clock	Rising Clock Edge
CE	Clock Enable	Active High
OCE[1]	Output Clock Enable	Active High
RST	Reset	Active High
BE[1]	Byte Enable	Active High
WE	Write Enable	Active High
AD	Address Bus	—
DI	Data In	—
DO	Data Out	—
CS	Chip Select	Active High
AFF	FIFO RAM Almost Full Flag	—
FF	FIFO RAM Full Flag	—
AEF	FIFO RAM Almost Empty Flag	—
EF	FIFO RAM Empty Flag	—
RPRST	FIFO RAM Read Pointer Reset	—

1. Optional signals.
2. For dual port EBR primitives a trailing ‘A’ or ‘B’ in the signal name specifies the EBR port A or port B respectively.
3. For FIFO RAM mode primitive, a trailing ‘R’ or ‘W’ in the signal name specifies the FIFO read port or write port respectively.
4. For FIFO RAM mode primitive FULLI has the same function as CSW(2) and EMPTYI has the same function as CSR(2).
5. In FIFO mode, CLKW is the write port clock, CSW is the write port chip select, CLKR is the read port clock, CSR is the read port chip select, ORE is the output read enable.

DDR Memory Support

Certain PICs on the right edge of MachXO2-640U, MachXO2-1200/U and larger devices, have additional circuitry to allow the implementation of DDR memory interfaces. There are two groups of 14 or 12 PIOs each on the right edge with additional circuitry to implement DDR memory interfaces. This capability allows the implementation of up to 16-bit wide memory interfaces. One PIO from each group contains a control element, the DQS Read/Write Block, to facilitate the generation of clock and control signals (DQSR90, DQSW90, DDRCLKPOL and DATAVALID). These clock and control signals are distributed to the other PIO in the group through dedicated low skew routing.

DQS Read Write Block

Source synchronous interfaces generally require the input clock to be adjusted in order to correctly capture data at the input register. For most interfaces a PLL is used for this adjustment. However, in DDR memories the clock (referred to as DQS) is not free-running so this approach cannot be used. The DQS Read Write block provides the required clock alignment for DDR memory interfaces. DQSR90 and DQSW90 signals are generated by the DQS Read Write block from the DQS input.

In a typical DDR memory interface design, the phase relationship between the incoming delayed DQS strobe and the internal system clock (during the read cycle) is unknown. The MachXO2 family contains dedicated circuits to transfer data between these domains. To prevent set-up and hold violations, at the domain transfer between DQS (delayed) and the system clock, a clock polarity selector is used. This circuit changes the edge on which the data is registered in the synchronizing registers in the input register block. This requires evaluation at the start of each read cycle for the correct clock polarity. Prior to the read operation in DDR memories, DQS is in tri-state (pulled by termination). The DDR memory device drives DQS low at the start of the preamble state. A dedicated circuit in the DQS Read Write block detects the first DQS rising edge after the preamble state and generates the DDRCLKPOL signal. This signal is used to control the polarity of the clock to the synchronizing registers.

The temperature, voltage and process variations of the DQS delay block are compensated by a set of calibration signals (6-bit bus) from a DLL on the right edge of the device. The DLL loop is compensated for temperature, voltage and process variations by the system clock and feedback loop.

sysIO Buffer

Each I/O is associated with a flexible buffer referred to as a sysIO buffer. These buffers are arranged around the periphery of the device in groups referred to as banks. The sysIO buffers allow users to implement a wide variety of standards that are found in today's systems including LVCMOS, TTL, PCI, SSTL, HSTL, LVDS, BLVDS, MLVDS and LVPECL.

Each bank is capable of supporting multiple I/O standards. In the MachXO2 devices, single-ended output buffers, ratioed input buffers (LVTTL, LVCMOS and PCI), differential (LVDS) and referenced input buffers (SSTL and HSTL) are powered using I/O supply voltage (V_{CCIO}). Each sysIO bank has its own V_{CCIO}. In addition, each bank has a voltage reference, V_{REF}, which allows the use of referenced input buffers independent of the bank V_{CCIO}.

MachXO2-256 and MachXO2-640 devices contain single-ended ratioed input buffers and single-ended output buffers with complementary outputs on all the I/O banks. Note that the single-ended input buffers on these devices do not contain PCI clamps. In addition to the single-ended I/O buffers these two devices also have differential and referenced input buffers on all I/Os. The I/Os are arranged in pairs, the two pads in the pair are described as “T” and “C”, where the true pad is associated with the positive side of the differential input buffer and the comp (complementary) pad is associated with the negative side of the differential input buffer.

Table 2-11. I/O Support Device by Device

	MachXO2-256, MachXO2-640	**MachXO2-640U, MachXO2-1200**	**MachXO2-1200U MachXO2-2000/U, MachXO2-4000, MachXO2-7000**
Number of I/O Banks	4	4	6
Type of Input Buffers	Single-ended (all I/O banks) Differential Receivers (all I/O banks)	Single-ended (all I/O banks) Differential Receivers (all I/O banks) Differential input termination (bottom side)	Single-ended (all I/O banks) Differential Receivers (all I/O banks) Differential input termination (bottom side)
Types of Output Buffers	Single-ended buffers with complementary outputs (all I/O banks)	Single-ended buffers with complementary outputs (all I/O banks) Differential buffers with true LVDS outputs (50% on top side)	Single-ended buffers with complementary outputs (all I/O banks) Differential buffers with true LVDS outputs (50% on top side)
Differential Output Emulation Capability	All I/O banks	All I/O banks	All I/O banks
PCI Clamp Support	No	Clamp on bottom side only	Clamp on bottom side only

Table 2-12. Supported Input Standards

	VCCIO (Typ.)				
Input Standard	**3.3 V**	**2.5 V**	**1.8 V**	**1.5**	**1.2 V**
Single-Ended Interfaces					
LVTTL	✓	✓[2]	✓[2]	✓[2]	
LVCMOS33	✓	✓[2]	✓[2]	✓[2]	
LVCMOS25	✓[2]	✓	✓[2]	✓[2]	
LVCMOS18	✓[2]	✓[2]	✓	✓[2]	
LVCMOS15	✓[2]	✓[2]	✓[2]	✓	✓[2]
LVCMOS12	✓[2]	✓[2]	✓[2]	✓[2]	✓
PCI[1]	✓				
SSTL18 (Class I, Class II)	✓	✓	✓		
SSTL25 (Class I, Class II)	✓	✓			
HSTL18 (Class I, Class II)	✓	✓	✓		
Differential Interfaces					
LVDS	✓	✓			
BLVDS, MVDS, LVPECL, RSDS	✓	✓			
MIPI[3]	✓	✓			
Differential SSTL18 Class I, II	✓	✓	✓		
Differential SSTL25 Class I, II	✓	✓			
Differential HSTL18 Class I, II	✓	✓	✓		

1. Bottom banks of MachXO2-640U, MachXO2-1200/U and higher density devices only.
2. Reduced functionality. Refer to TN1202, MachXO2 sysIO Usage Guide for more detail.
3. These interfaces can be emulated with external resistors in all devices.

Figure 2-18. MachXO2-1200U, MachXO2-2000/U, MachXO2-4000 and MachXO2-7000 Banks

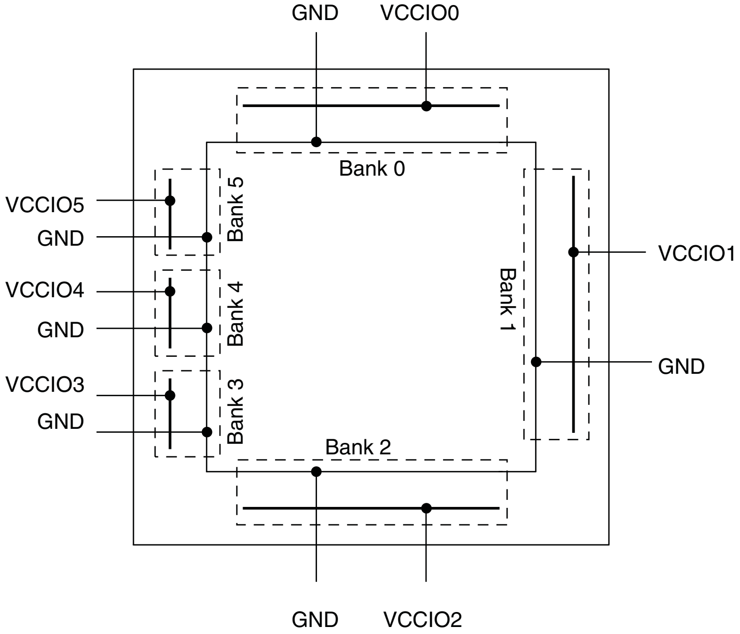
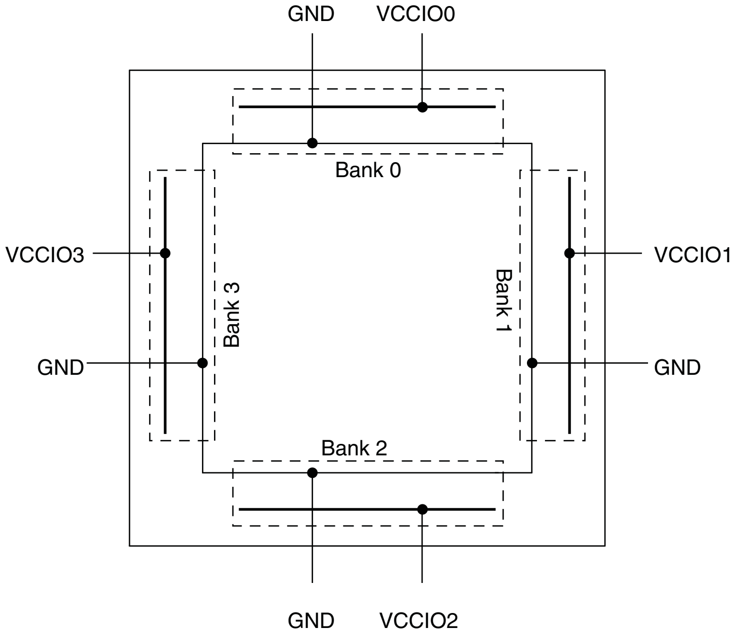


Figure 2-19. MachXO2-256, MachXO2-640/U and MachXO2-1200 Banks



There are some limitations on the use of the hardened user SPI. These are defined in the following technical notes:

- TN1087, Minimizing System Interruption During Configuration Using TransFR Technology (Appendix B)
- TN1205, Using User Flash Memory and Hardened Control Functions in MachXO2 Devices

Figure 2-22. SPI Core Block Diagram

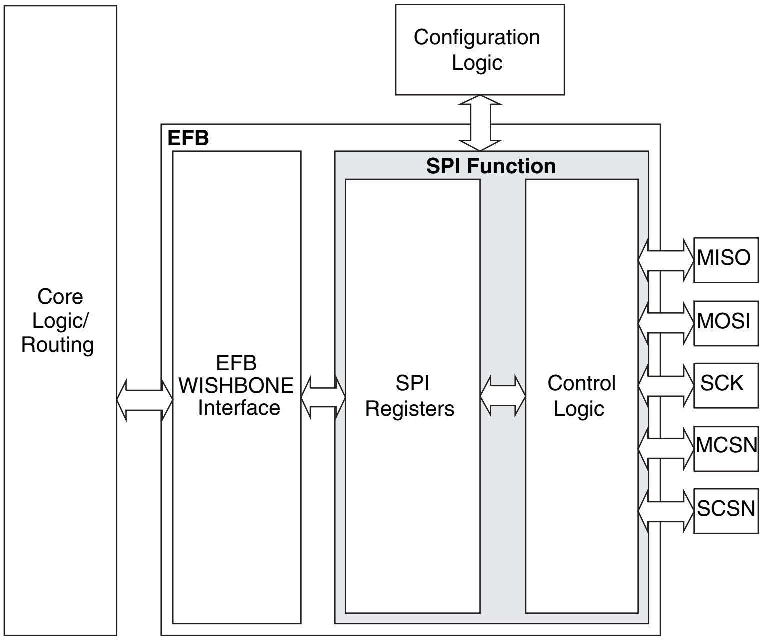


Table 2-16 describes the signals interfacing with the SPI cores.

Table 2-16. SPI Core Signal Description

Signal Name	I/O	Master/Slave	Description
spi_csn[0]	O	Master	SPI master chip-select output
spi_csn[1..7]	O	Master	Additional SPI chip-select outputs (total up to eight slaves)
spi_scsn	I	Slave	SPI slave chip-select input
spi_irq	O	Master/Slave	Interrupt request
spi_clk	I/O	Master/Slave	SPI clock. Output in master mode. Input in slave mode.
spi_miso	I/O	Master/Slave	SPI data. Input in master mode. Output in slave mode.
spi_mosi	I/O	Master/Slave	SPI data. Output in master mode. Input in slave mode.
ufm_sn	I	Slave	Configuration Slave Chip Select (active low), dedicated for selecting the User Flash Memory (UFM).
cfg_stdby	O	Master/Slave	Stand-by signal – To be connected only to the power module of the MachXO2 device. The signal is enabled only if the “Wakeup Enable” feature has been set within the EFB GUI, SPI Tab.
cfg_wake	O	Master/Slave	Wake-up signal – To be connected only to the power module of the MachXO2 device. The signal is enabled only if the “Wakeup Enable” feature has been set within the EFB GUI, SPI Tab.

DC Electrical Characteristics

Over Recommended Operating Conditions

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
I_{IL}, I_{IH}[1, 4]	Input or I/O Leakage	Clamp OFF and $V_{CCIO} < V_{IN} < V_{IH}$ (MAX)	—	—	+175	µA
		Clamp OFF and $V_{IN} = V_{CCIO}$	–10	—	10	µA
		Clamp OFF and V_{CCIO} –0.97 V < V_{IN} < V_{CCIO}	–175	—	—	µA
		Clamp OFF and 0 V < V_{IN} < V_{CCIO} –0.97 V	—	—	10	µA
		Clamp OFF and V_{IN} = GND	—	—	10	µA
		Clamp ON and 0 V < V_{IN} < V_{CCIO}	—	—	10	µA
I_{PU}	I/O Active Pull-up Current	$0 < V_{IN} < 0.7\ V_{CCIO}$	–30	—	-309	µA
I_{PD}	I/O Active Pull-down Current	V_{IL} (MAX) < $V_{IN} < V_{CCIO}$	30	—	305	µA
I_{BHLS}	Bus Hold Low sustaining current	$V_{IN} = V_{IL}$ (MAX)	30	—	—	µA
I_{BHHS}	Bus Hold High sustaining current	$V_{IN} = 0.7V_{CCIO}$	–30	—	—	µA
I_{BHLO}	Bus Hold Low Overdrive current	$0 \leq V_{IN} \leq V_{CCIO}$	—	—	305	µA
I_{BHHO}	Bus Hold High Overdrive current	$0 \leq V_{IN} \leq V_{CCIO}$	—	—	–309	µA
V_{BHT}[3]	Bus Hold Trip Points		V_{IL} (MAX)	—	V_{IH} (MIN)	V
C1	I/O Capacitance[2]	V_{CCIO} = 3.3 V, 2.5 V, 1.8 V, 1.5 V, 1.2 V, V_{CC} = Typ., V_{IO} = 0 to V_{IH} (MAX)	3	5	9	pF
C2	Dedicated Input Capacitance[2]	V_{CCIO} = 3.3 V, 2.5 V, 1.8 V, 1.5 V, 1.2 V, V_{CC} = Typ., V_{IO} = 0 to V_{IH} (MAX)	3	5.5	7	pF
V_{HYST}	Hysteresis for Schmitt Trigger Inputs[5]	V_{CCIO} = 3.3 V, Hysteresis = Large	—	450	—	mV
		V_{CCIO} = 2.5 V, Hysteresis = Large	—	250	—	mV
		V_{CCIO} = 1.8 V, Hysteresis = Large	—	125	—	mV
		V_{CCIO} = 1.5 V, Hysteresis = Large	—	100	—	mV
		V_{CCIO} = 3.3 V, Hysteresis = Small	—	250	—	mV
		V_{CCIO} = 2.5 V, Hysteresis = Small	—	150	—	mV
		V_{CCIO} = 1.8 V, Hysteresis = Small	—	60	—	mV
		V_{CCIO} = 1.5 V, Hysteresis = Small	—	40	—	mV

1. Input or I/O leakage current is measured with the pin configured as an input or as an I/O with the output driver tri-stated. It is not measured with the output driver active. Bus maintenance circuits are disabled.
2. T_A 25 °C, f = 1.0 MHz.
3. Please refer to V_{IL} and V_{IH} in the sysIO Single-Ended DC Electrical Characteristics table of this document.
4. When V_{IH} is higher than V_{CCIO}, a transient current typically of 30 ns in duration or less with a peak current of 6 mA can occur on the high-to-low transition. For true LVDS output pins in MachXO2-640U, MachXO2-1200/U and larger devices, V_{IH} must be less than or equal to V_{CCIO}.
5. With bus keeper circuit turned on. For more details, refer to TN1202, MachXO2 sysIO Usage Guide.

Programming and Erase Flash Supply Current – ZE Devices[1, 2, 3, 4]

Symbol	Parameter	Device	Typ.[5]	Units
I_{CC}	Core Power Supply	LCMXO2-256ZE	13	mA
		LCMXO2-640ZE	14	mA
		LCMXO2-1200ZE	15	mA
		LCMXO2-2000ZE	17	mA
		LCMXO2-4000ZE	18	mA
		LCMXO2-7000ZE	20	mA
I_{CCIO}	Bank Power Supply[6]	All devices	0	mA

1. For further information on supply current, please refer to TN1198, Power Estimation and Management for MachXO2 Devices.
2. Assumes all inputs are held at V_{CCIO} or GND and all outputs are tri-stated.
3. Typical user pattern.
4. JTAG programming is at 25 MHz.
5. TJ = 25 °C, power supplies at nominal voltage.
6. Per bank. V_{CCIO} = 2.5 V. Does not include pull-up/pull-down.

sysIO Recommended Operating Conditions

Standard	V_{CCIO} (V)			V_{REF} (V)		
	Min.	Typ.	Max.	Min.	Typ.	Max.
LVCMOS 3.3	3.135	3.3	3.6	—	—	—
LVCMOS 2.5	2.375	2.5	2.625	—	—	—
LVCMOS 1.8	1.71	1.8	1.89	—	—	—
LVCMOS 1.5	1.425	1.5	1.575	—	—	—
LVCMOS 1.2	1.14	1.2	1.26	—	—	—
LVTTL	3.135	3.3	3.6	—	—	—
PCI[3]	3.135	3.3	3.6	—	—	—
SSTL25	2.375	2.5	2.625	1.15	1.25	1.35
SSTL18	1.71	1.8	1.89	0.833	0.9	0.969
HSTL18	1.71	1.8	1.89	0.816	0.9	1.08
LVCMOS25R33	3.135	3.3	3.6	1.1	1.25	1.4
LVCMOS18R33	3.135	3.3	3.6	0.75	0.9	1.05
LVCMOS18R25	2.375	2.5	2.625	0.75	0.9	1.05
LVCMOS15R33	3.135	3.3	3.6	0.6	0.75	0.9
LVCMOS15R25	2.375	2.5	2.625	0.6	0.75	0.9
LVCMOS12R33[4]	3.135	3.3	3.6	0.45	0.6	0.75
LVCMOS12R25[4]	2.375	2.5	2.625	0.45	0.6	0.75
LVCMOS10R33[4]	3.135	3.3	3.6	0.35	0.5	0.65
LVCMOS10R25[4]	2.375	2.5	2.625	0.35	0.5	0.65
LVDS25[1, 2]	2.375	2.5	2.625	—	—	—
LVDS33[1, 2]	3.135	3.3	3.6	—	—	—
LVPECL[1]	3.135	3.3	3.6	—	—	—
BLVDS[1]	2.375	2.5	2.625	—	—	—
RSDS[1]	2.375	2.5	2.625	—	—	—
SSTL18D	1.71	1.8	1.89	—	—	—
SSTL25D	2.375	2.5	2.625	—	—	—
HSTL18D	1.71	1.8	1.89	—	—	—

1. Inputs on-chip. Outputs are implemented with the addition of external resistors.
2. MachXO2-640U, MachXO2-1200/U and larger devices have dedicated LVDS buffers.
3. Input on the bottom bank of the MachXO2-640U, MachXO2-1200/U and larger devices only.
4. Supported only for inputs and BIDIs for all ZE devices, and –6 speed grade for HE and HC devices.

RSDS

The MachXO2 family supports the differential RSDS standard. The output standard is emulated using complementary LVCMOS outputs in conjunction with resistors across the driver outputs on all the devices. The RSDS input standard is supported by the LVDS differential input buffer. The scheme shown in Figure 3-4 is one possible solution for RSDS standard implementation. Use LVDS25E mode with suggested resistors for RSDS operation. Resistor values in Figure 3-4 are industry standard values for 1% resistors.

Figure 3-4. RSDS (Reduced Swing Differential Standard)

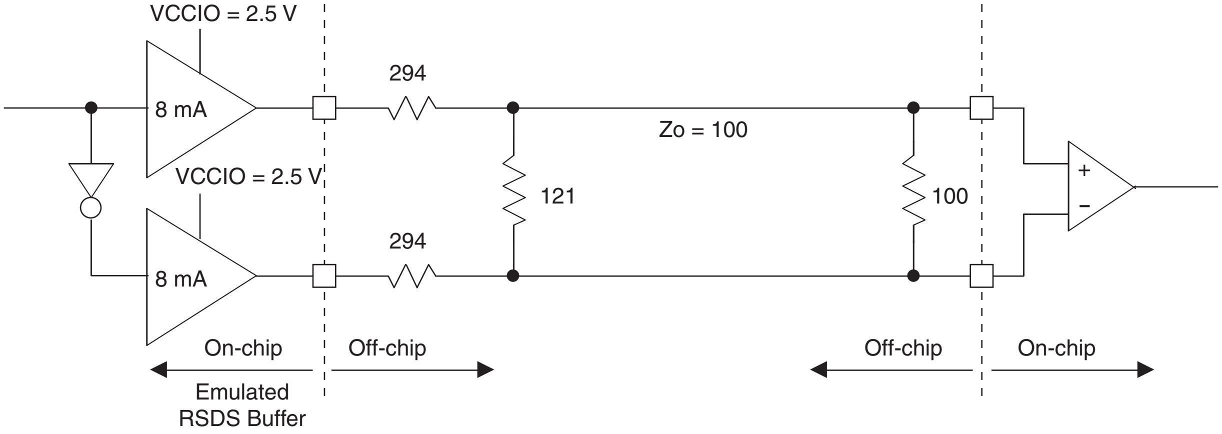


Table 3-4. RSDS DC Conditions

Parameter	Description	Typical	Units
Z_{OUT}	Output impedance	20	Ohms
R_S	Driver series resistor	294	Ohms
R_P	Driver parallel resistor	121	Ohms
R_T	Receiver termination	100	Ohms
V_{OH}	Output high voltage	1.35	V
V_{OL}	Output low voltage	1.15	V
V_{OD}	Output differential voltage	0.20	V
V_{CM}	Output common mode voltage	1.25	V
Z_{BACK}	Back impedance	101.5	Ohms
I_{DC}	DC output current	3.66	mA

Parameter	Description	Device	–6		–5		–4		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
LPDDR[9, 12]									
t_{DVADQ}	Input Data Valid After DQS Input	MachXO2-1200/U and larger devices, right side only.[13]	—	0.369	—	0.395	—	0.421	UI
t_{DVEDQ}	Input Data Hold After DQS Input		0.529	—	0.530	—	0.527	—	UI
t_{DQVBS}	Output Data Invalid Before DQS Output		0.25	—	0.25	—	0.25	—	UI
t_{DQVAS}	Output Data Invalid After DQS Output		0.25	—	0.25	—	0.25	—	UI
f_{DATA}	MEM LPDDR Serial Data Speed		—	280	—	250	—	208	Mbps
f_{SCLK}	SCLK Frequency		—	140	—	125	—	104	MHz
f_{LPDDR}	LPDDR Data Transfer Rate		0	280	0	250	0	208	Mbps
DDR[9, 12]									
t_{DVADQ}	Input Data Valid After DQS Input	MachXO2-1200/U and larger devices, right side only.[13]	—	0.350	—	0.387	—	0.414	UI
t_{DVEDQ}	Input Data Hold After DQS Input		0.545	—	0.538	—	0.532	—	UI
t_{DQVBS}	Output Data Invalid Before DQS Output		0.25	—	0.25	—	0.25	—	UI
t_{DQVAS}	Output Data Invalid After DQS Output		0.25	—	0.25	—	0.25	—	UI
f_{DATA}	MEM DDR Serial Data Speed		—	300	—	250	—	208	Mbps
f_{SCLK}	SCLK Frequency		—	150	—	125	—	104	MHz
f_{MEM_DDR}	MEM DDR Data Transfer Rate		N/A	300	N/A	250	N/A	208	Mbps
DDR2[9, 12]									
t_{DVADQ}	Input Data Valid After DQS Input	MachXO2-1200/U and larger devices, right side only.[13]	—	0.360	—	0.378	—	0.406	UI
t_{DVEDQ}	Input Data Hold After DQS Input		0.555	—	0.549	—	0.542	—	UI
t_{DQVBS}	Output Data Invalid Before DQS Output		0.25	—	0.25	—	0.25	—	UI
t_{DQVAS}	Output Data Invalid After DQS Output		0.25	—	0.25	—	0.25	—	UI
f_{DATA}	MEM DDR Serial Data Speed		—	300	—	250	—	208	Mbps
f_{SCLK}	SCLK Frequency		—	150	—	125	—	104	MHz
f_{MEM_DDR2}	MEM DDR2 Data Transfer Rate		N/A	300	N/A	250	N/A	208	Mbps

1. Exact performance may vary with device and design implementation. Commercial timing numbers are shown at 85 °C and 1.14 V. Other operating conditions, including industrial, can be extracted from the Diamond software.
2. General I/O timing numbers based on LVCMOS 2.5, 8 mA, 0pf load, fast slew rate.
3. Generic DDR timing numbers based on LVDS I/O (for input, output, and clock ports).
4. DDR timing numbers based on SSTL25. DDR2 timing numbers based on SSTL18. LPDDR timing numbers based in LVCMOS18.
5. 7:1 LVDS (GDDR71) uses the LVDS I/O standard (for input, output, and clock ports).
6. For Generic DDRX1 mode $t_{SU} = t_{HO} = (t_{DVE} - t_{DVA} - 0.03\text{ ns})/2$.
7. The t_{SU_DEL} and t_{H_DEL} values use the SCLK_ZERHOLD default step size. Each step is 105 ps (–6), 113 ps (–5), 120 ps (–4).
8. This number for general purpose usage. Duty cycle tolerance is +/– 10%.
9. Duty cycle is +/–5% for system usage.
10. The above timing numbers are generated using the Diamond design tool. Exact performance may vary with the device selected.
11. High-speed DDR and LVDS not supported in SG32 (32 QFN) packages.
12. Advance information for MachXO2 devices in 48 QFN packages.
13. DDR memory interface not supported in QN84 (84 QFN) and SG32 (32 QFN) packages.

Figure 3-5. Receiver RX.CLK.Aligned and MEM DDR Input Waveforms

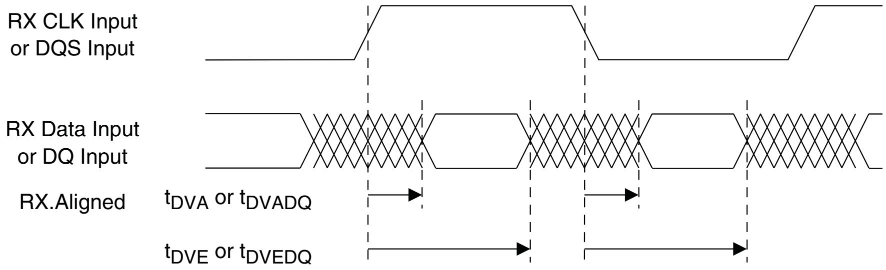


Figure 3-6. Receiver RX.CLK.Centered Waveforms

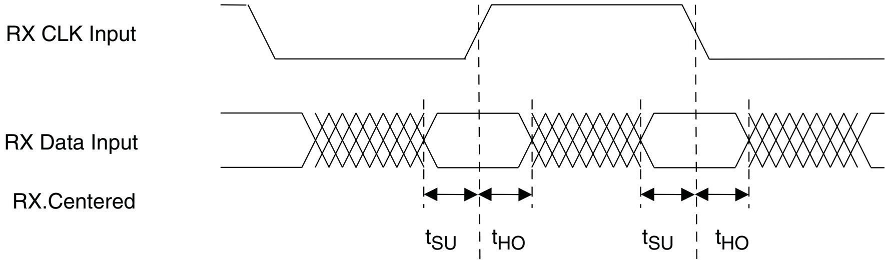


Figure 3-7. Transmitter TX.CLK.Aligned Waveforms

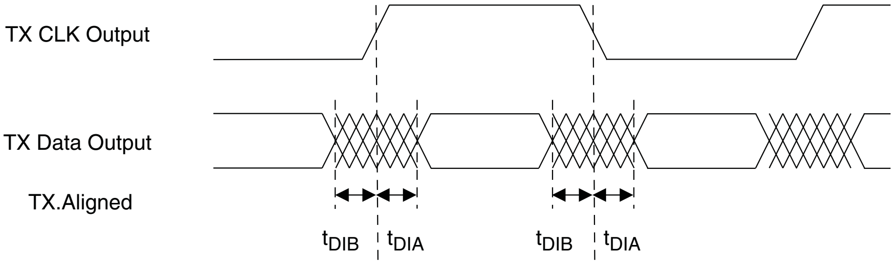
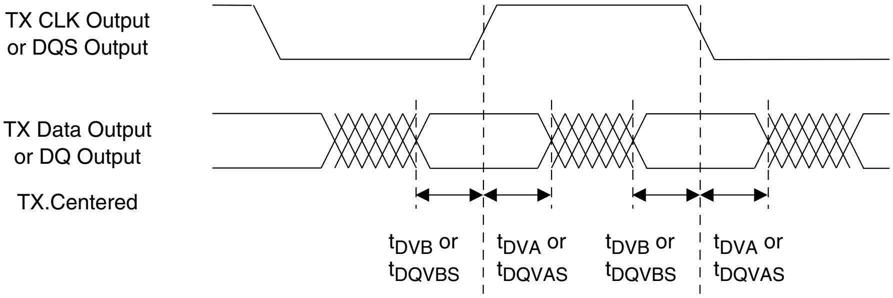


Figure 3-8. Transmitter TX.CLK.Centered and MEM DDR Output Waveforms



sysCLOCK PLL Timing

Over Recommended Operating Conditions

Parameter	Descriptions	Conditions	Min.	Max.	Units
f_{IN}	Input Clock Frequency (CLKI, CLKFB)		7	400	MHz
f_{OUT}	Output Clock Frequency (CLKOP, CLKOS, CLKOS2)		1.5625	400	MHz
f_{OUT2}	Output Frequency (CLKOS3 cascaded from CLKOS2)		0.0122	400	MHz
f_{VCO}	PLL VCO Frequency		200	800	MHz
f_{PFD}	Phase Detector Input Frequency		7	400	MHz
AC Characteristics					
t_{DT}	Output Clock Duty Cycle	Without duty trim selected[3]	45	55	%
t_{DT_TRIM}[7]	Edge Duty Trim Accuracy		–75	75	%
t_{PH}[4]	Output Phase Accuracy		–6	6	%
t_{OPJIT}[1, 8]	Output Clock Period Jitter	f_{OUT} > 100 MHz	—	150	ps p-p
		f_{OUT} < 100 MHz	—	0.007	UIPP
	Output Clock Cycle-to-cycle Jitter	f_{OUT} > 100 MHz	—	180	ps p-p
		f_{OUT} < 100 MHz	—	0.009	UIPP
	Output Clock Phase Jitter	f_{PFD} > 100 MHz	—	160	ps p-p
		f_{PFD} < 100 MHz	—	0.011	UIPP
	Output Clock Period Jitter (Fractional-N)	f_{OUT} > 100 MHz	—	230	ps p-p
		f_{OUT} < 100 MHz	—	0.12	UIPP
	Output Clock Cycle-to-cycle Jitter (Fractional-N)	f_{OUT} > 100 MHz	—	230	ps p-p
		f_{OUT} < 100 MHz	—	0.12	UIPP
t_{SPO}	Static Phase Offset	Divider ratio = integer	–120	120	ps
t_{W}	Output Clock Pulse Width	At 90% or 10%[3]	0.9	—	ns
t_{LOCK}[2, 5]	PLL Lock-in Time		—	15	ms
t_{UNLOCK}	PLL Unlock Time		—	50	ns
t_{IPJIT}[6]	Input Clock Period Jitter	$f_{PFD} \geq 20$ MHz	—	1,000	ps p-p
		f_{PFD} < 20 MHz	—	0.02	UIPP
t_{HI}	Input Clock High Time	90% to 90%	0.5	—	ns
t_{LO}	Input Clock Low Time	10% to 10%	0.5	—	ns
t_{STABLE}[5]	STANDBY High to PLL Stable		—	15	ms
t_{RST}	RST/RESETM Pulse Width		1	—	ns
t_{RSTREC}	RST Recovery Time		1	—	ns
t_{RST_DIV}	RESETC/D Pulse Width		10	—	ns
t_{RSTREC_DIV}	RESETC/D Recovery Time		1	—	ns
$t_{ROTATE\text{-}SETUP}$	PHASESTEP Setup Time		10	—	ns

I²C Port Timing Specifications[1, 2]

Symbol	Parameter	Min.	Max.	Units
f_{MAX}	Maximum SCL clock frequency	—	400	kHz

1. MachXO2 supports the following modes:
   - Standard-mode (Sm), with a bit rate up to 100 kbit/s (user and configuration mode)
   - Fast-mode (Fm), with a bit rate up to 400 kbit/s (user and configuration mode)
2. Refer to the I²C specification for timing requirements.

SPI Port Timing Specifications[1]

Symbol	Parameter	Min.	Max.	Units
f_{MAX}	Maximum SCK clock frequency	—	45	MHz

1. Applies to user mode only. For configuration mode timing specifications, refer to sysCONFIG Port Timing Specifications table in this data sheet.

Switching Test Conditions

Figure 3-13 shows the output test load used for AC testing. The specific values for resistance, capacitance, voltage, and other test conditions are shown in Table 3-5.

Figure 3-13. Output Test Load, LVTTL and LVCMOS Standards

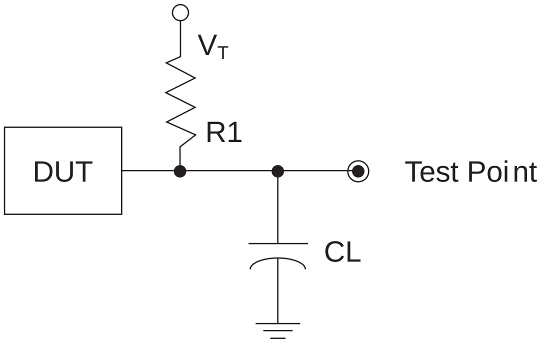


Table 3-5. Test Fixture Required Components, Non-Terminated Interfaces

Test Condition	R1	CL	Timing Ref.	VT
LVTTL and LVCMOS settings (L -> H, H -> L)	∞	0pF	LVTTL, LVCMOS 3.3 = 1.5 V	—
			LVCMOS 2.5 = $V_{CCIO}/2$	—
			LVCMOS 1.8 = $V_{CCIO}/2$	—
			LVCMOS 1.5 = $V_{CCIO}/2$	—
			LVCMOS 1.2 = $V_{CCIO}/2$	—
LVTTL and LVCMOS 3.3 (Z -> H)	188	0pF	1.5 V	V_{OL}
LVTTL and LVCMOS 3.3 (Z -> L)			1.5 V	V_{OH}
Other LVCMOS (Z -> H)			$V_{CCIO}/2$	V_{OL}
Other LVCMOS (Z -> L)			$V_{CCIO}/2$	V_{OH}
LVTTL + LVCMOS (H -> Z)			$V_{OH} – 0.15$ V	V_{OL}
LVTTL + LVCMOS (L -> Z)			$V_{OL} – 0.15$ V	V_{OH}

Note: Output test conditions for all other interfaces are determined by the respective standards.

	MachXO2-2000						MachXO2-2000U
	49 WLCSP	**100 TQFP**	**132 csBGA**	**144 TQFP**	**256 caBGA**	**256 ftBGA**	**484 ftBGA**
General Purpose I/O per Bank							
Bank 0	19	18	25	27	50	50	70
Bank 1	0	21	26	28	52	52	68
Bank 2	13	20	28	28	52	52	72
Bank 3	0	6	7	8	16	16	24
Bank 4	0	6	8	10	16	16	16
Bank 5	6	8	10	10	20	20	28
Total General Purpose Single-Ended I/O	38	79	104	111	206	206	278
Differential I/O per Bank							
Bank 0	7	9	13	14	25	25	35
Bank 1	0	10	13	14	26	26	34
Bank 2	6	10	14	14	26	26	36
Bank 3	0	3	3	4	8	8	12
Bank 4	0	3	4	5	8	8	8
Bank 5	3	4	5	5	10	10	14
Total General Purpose Differential I/O	16	39	52	56	103	103	139
Dual Function I/O	24	31	33	33	33	33	37
High-speed Differential I/O							
Bank 0	5	4	8	9	14	14	18
Gearboxes							
Number of 7:1 or 8:1 Output Gearbox Available (Bank 0)	5	4	8	9	14	14	18
Number of 7:1 or 8:1 Input Gearbox Available (Bank 2)	6	10	14	14	14	14	18
DQS Groups							
Bank 1	0	1	2	2	2	2	2
VCCIO Pins							
Bank 0	2	2	3	3	4	4	10
Bank 1	0	2	3	3	4	4	10
Bank 2	1	2	3	3	4	4	10
Bank 3	0	1	1	1	1	1	3
Bank 4	0	1	1	1	2	2	4
Bank 5	1	1	1	1	1	1	3
VCC	2	2	4	4	8	8	12
GND	4	8	10	12	24	24	48
NC	0	1	1	4	1	1	105
Reserved for Configuration	1	1	1	1	v	1	1
Total Count of Bonded Pins	39	100	132	144	256	256	484

	MachXO2-7000					
	144 TQFP	256 caBGA	256 ftBGA	332 caBGA	400 caBGA	484 fpBGA
General Purpose I/O per Bank						
Bank 0	27	50	50	68	83	82
Bank 1	29	52	52	70	84	84
Bank 2	29	52	52	70	84	84
Bank 3	9	16	16	24	28	28
Bank 4	10	16	16	16	24	24
Bank 5	10	20	20	30	32	32
Total General Purpose Single Ended I/O	114	206	206	278	335	334
Differential I/O per Bank						
Bank 0	14	25	25	34	42	41
Bank 1	14	26	26	35	42	42
Bank 2	14	26	26	35	42	42
Bank 3	4	8	8	12	14	14
Bank 4	5	8	8	8	12	12
Bank 5	5	10	10	15	16	16
Total General Purpose Differential I/O	56	103	103	139	168	167
Dual Function I/O	37	37	37	37	37	37
High-speed Differential I/O						
Bank 0	9	20	20	21	21	21
Gearboxes						
Number of 7:1 or 8:1 Output Gearbox Available (Bank 0)	9	20	20	21	21	21
Number of 7:1 or 8:1 Input Gearbox Available (Bank 2)	14	20	20	21	21	21
DQS Groups						
Bank 1	2	2	2	2	2	2
VCCIO Pins						
Bank 0	3	4	4	4	5	10
Bank 1	3	4	4	4	5	10
Bank 2	3	4	4	4	5	10
Bank 3	1	1	1	2	2	3
Bank 4	1	2	2	1	2	4
Bank 5	1	1	1	2	2	3
VCC	4	8	8	8	10	12
GND	12	24	24	27	33	48
NC	1	1	1	1	0	49
Reserved for Configuration	1	1	1	1	1	1
Total Count of Bonded Pins	144	256	256	332	400	484

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-2000ZE-1TG100C	2112	1.2 V	–1	Halogen-Free TQFP	100	COM
LCMXO2-2000ZE-2TG100C	2112	1.2 V	–2	Halogen-Free TQFP	100	COM
LCMXO2-2000ZE-3TG100C	2112	1.2 V	–3	Halogen-Free TQFP	100	COM
LCMXO2-2000ZE-1MG132C	2112	1.2 V	–1	Halogen-Free csBGA	132	COM
LCMXO2-2000ZE-2MG132C	2112	1.2 V	–2	Halogen-Free csBGA	132	COM
LCMXO2-2000ZE-3MG132C	2112	1.2 V	–3	Halogen-Free csBGA	132	COM
LCMXO2-2000ZE-1TG144C	2112	1.2 V	–1	Halogen-Free TQFP	144	COM
LCMXO2-2000ZE-2TG144C	2112	1.2 V	–2	Halogen-Free TQFP	144	COM
LCMXO2-2000ZE-3TG144C	2112	1.2 V	–3	Halogen-Free TQFP	144	COM
LCMXO2-2000ZE-1BG256C	2112	1.2 V	–1	Halogen-Free caBGA	256	COM
LCMXO2-2000ZE-2BG256C	2112	1.2 V	–2	Halogen-Free caBGA	256	COM
LCMXO2-2000ZE-3BG256C	2112	1.2 V	–3	Halogen-Free caBGA	256	COM
LCMXO2-2000ZE-1FTG256C	2112	1.2 V	–1	Halogen-Free ftBGA	256	COM
LCMXO2-2000ZE-2FTG256C	2112	1.2 V	–2	Halogen-Free ftBGA	256	COM
LCMXO2-2000ZE-3FTG256C	2112	1.2 V	–3	Halogen-Free ftBGA	256	COM

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-4000ZE-1QN84C	4320	1.2 V	–1	Halogen-Free QFN	84	COM
LCMXO2-4000ZE-2QN84C	4320	1.2 V	–2	Halogen-Free QFN	84	COM
LCMXO2-4000ZE-3QN84C	4320	1.2 V	–3	Halogen-Free QFN	84	COM
LCMXO2-4000ZE-1MG132C	4320	1.2 V	–1	Halogen-Free csBGA	132	COM
LCMXO2-4000ZE-2MG132C	4320	1.2 V	–2	Halogen-Free csBGA	132	COM
LCMXO2-4000ZE-3MG132C	4320	1.2 V	–3	Halogen-Free csBGA	132	COM
LCMXO2-4000ZE-1TG144C	4320	1.2 V	–1	Halogen-Free TQFP	144	COM
LCMXO2-4000ZE-2TG144C	4320	1.2 V	–2	Halogen-Free TQFP	144	COM
LCMXO2-4000ZE-3TG144C	4320	1.2 V	–3	Halogen-Free TQFP	144	COM
LCMXO2-4000ZE-1BG256C	4320	1.2 V	–1	Halogen-Free caBGA	256	COM
LCMXO2-4000ZE-2BG256C	4320	1.2 V	–2	Halogen-Free caBGA	256	COM
LCMXO2-4000ZE-3BG256C	4320	1.2 V	–3	Halogen-Free caBGA	256	COM
LCMXO2-4000ZE-1FTG256C	4320	1.2 V	–1	Halogen-Free ftBGA	256	COM
LCMXO2-4000ZE-2FTG256C	4320	1.2 V	–2	Halogen-Free ftBGA	256	COM
LCMXO2-4000ZE-3FTG256C	4320	1.2 V	–3	Halogen-Free ftBGA	256	COM
LCMXO2-4000ZE-1BG332C	4320	1.2 V	–1	Halogen-Free caBGA	332	COM
LCMXO2-4000ZE-2BG332C	4320	1.2 V	–2	Halogen-Free caBGA	332	COM
LCMXO2-4000ZE-3BG332C	4320	1.2 V	–3	Halogen-Free caBGA	332	COM
LCMXO2-4000ZE-1FG484C	4320	1.2 V	–1	Halogen-Free fpBGA	484	COM
LCMXO2-4000ZE-2FG484C	4320	1.2 V	–2	Halogen-Free fpBGA	484	COM
LCMXO2-4000ZE-3FG484C	4320	1.2 V	–3	Halogen-Free fpBGA	484	COM

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-1200ZE-1TG100IR1[1]	1280	1.2 V	–1	Halogen-Free TQFP	100	IND
LCMXO2-1200ZE-2TG100IR1[1]	1280	1.2 V	–2	Halogen-Free TQFP	100	IND
LCMXO2-1200ZE-3TG100IR1[1]	1280	1.2 V	–3	Halogen-Free TQFP	100	IND
LCMXO2-1200ZE-1MG132IR1[1]	1280	1.2 V	–1	Halogen-Free csBGA	132	IND
LCMXO2-1200ZE-2MG132IR1[1]	1280	1.2 V	–2	Halogen-Free csBGA	132	IND
LCMXO2-1200ZE-3MG132IR1[1]	1280	1.2 V	–3	Halogen-Free csBGA	132	IND
LCMXO2-1200ZE-1TG144IR1[1]	1280	1.2 V	–1	Halogen-Free TQFP	144	IND
LCMXO2-1200ZE-2TG144IR1[1]	1280	1.2 V	–2	Halogen-Free TQFP	144	IND
LCMXO2-1200ZE-3TG144IR1[1]	1280	1.2 V	–3	Halogen-Free TQFP	144	IND

1. Specifications for the “LCMXO2-1200ZE-speed package IR1” are the same as the “LCMXO2-1200ZE-speed package I” devices respectively, except as specified in the R1 Device Specifications section of this data sheet.

High Performance Industrial Grade Devices Without Voltage Regulator, Halogen Free (RoHS) Packaging

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-2000HE-4TG100I	2112	1.2 V	–4	Halogen-Free TQFP	100	IND
LCMXO2-2000HE-5TG100I	2112	1.2 V	–5	Halogen-Free TQFP	100	IND
LCMXO2-2000HE-6TG100I	2112	1.2 V	–6	Halogen-Free TQFP	100	IND
LCMXO2-2000HE-4MG132I	2112	1.2 V	–4	Halogen-Free csBGA	132	IND
LCMXO2-2000HE-5MG132I	2112	1.2 V	–5	Halogen-Free csBGA	132	IND
LCMXO2-2000HE-6MG132I	2112	1.2 V	–6	Halogen-Free csBGA	132	IND
LCMXO2-2000HE-4TG144I	2112	1.2 V	–4	Halogen-Free TQFP	144	IND
LCMXO2-2000HE-5TG144I	2112	1.2 V	–5	Halogen-Free TQFP	144	IND
LCMXO2-2000HE-6TG144I	2112	1.2 V	–6	Halogen-Free TQFP	144	IND
LCMXO2-2000HE-4BG256I	2112	1.2 V	–4	Halogen-Free caBGA	256	IND
LCMXO2-2000HE-5BG256I	2112	1.2 V	–5	Halogen-Free caBGA	256	IND
LCMXO2-2000HE-6BG256I	2112	1.2 V	–6	Halogen-Free caBGA	256	IND
LCMXO2-2000HE-4FTG256I	2112	1.2 V	–4	Halogen-Free ftBGA	256	IND
LCMXO2-2000HE-5FTG256I	2112	1.2 V	–5	Halogen-Free ftBGA	256	IND
LCMXO2-2000HE-6FTG256I	2112	1.2 V	–6	Halogen-Free ftBGA	256	IND

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-2000UHE-4FG484I	2112	1.2 V	–4	Halogen-Free fpBGA	484	IND
LCMXO2-2000UHE-5FG484I	2112	1.2 V	–5	Halogen-Free fpBGA	484	IND
LCMXO2-2000UHE-6FG484I	2112	1.2 V	–6	Halogen-Free fpBGA	484	IND

R1 Device Specifications

The LCMXO2-1200ZE/HC “R1” devices have the same specifications as their Standard (non-R1) counterparts except as listed below. For more details on the R1 to Standard migration refer to AN8086, Designing for Migration from MachXO2-1200-R1 to Standard Non-R1) Devices.

- The User Flash Memory (UFM) cannot be programmed through the internal WISHBONE interface. It can still be programmed through the JTAG/SPI/I^{2}C ports.
- The on-chip differential input termination resistor value is higher than intended. It is approximately 200Ω as opposed to the intended 100Ω. It is recommended to use external termination resistors for differential inputs. The on-chip termination resistors can be disabled through Lattice design software.
- Soft Error Detection logic may not produce the correct result when it is run for the first time after configuration. To use this feature, discard the result from the first operation. Subsequent operations will produce the correct result.
- Under certain conditions, IIH exceeds data sheet specifications. The following table provides more details:

Condition	Clamp	Pad Rising IIH Max.	Pad Falling IIH Min.	Steady State Pad High IIH	Steady State Pad Low IIL
VPAD > VCCIO	OFF	1 mA	–1 mA	1 mA	10 µA
VPAD = VCCIO	ON	10 µA	–10 µA	10 µA	10 µA
VPAD = VCCIO	OFF	1 mA	–1 mA	1 mA	10 µA
VPAD < VCCIO	OFF	10 µA	–10 µA	10 µA	10 µA

- The user SPI interface does not operate correctly in some situations. During master read access and slave write access, the last byte received does not generate the RRDY interrupt.
- In GDDRX2, GDDRX4 and GDDR71 modes, ECLKSYNC may have a glitch in the output under certain conditions, leading to possible loss of synchronization.
- When using the hard I^{2}C IP core, the I^{2}C status registers I2C_1_SR and I2C_2_SR may not update correctly.
- PLL Lock signal will glitch high when coming out of standby. This glitch lasts for about 10 µsec before returning low.
- Dual boot only available on HC devices, requires tying VCC and VCCIO2 to the same 3.3 V or 2.5 V supply.